

SILICON TRANSISTOR 2SD1583-Z

NPN SILICON EPITAXIAL TRANSISTOR MP-3

DESCRIPTION

2SD1583-Z is designed for Audio Frequency Amplifier and Switching, especially in Hybrid Integrated Circuits.

FEATURES

- High hre: hre= 800 to 3 200
- Low VCE(sat) VCE(sat) = 0.18 V TYP.

QUALITY GRADE

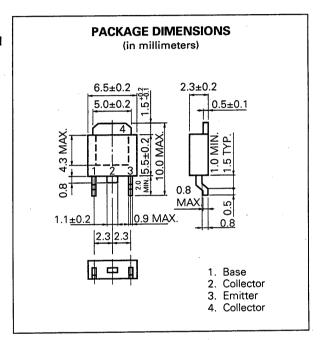
Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Collector to Base Voltage	Vсво	30	٧
Collector to Emitter Voltage	Vceo	20	٧
Emitter to Base Voltage	Vево	5	٧
Collector Current (DC)	lc	2	Α
Collector Current (Pulse)*	lc	' 3	Α
Total Power Dissipation (Ta = 25 °C)**	Рт	2.0	W
Junction Temperature	T_{j}	150	°C
Storage Temperature	Tstg	-55 to +150	°C

- * PW \leq 10 ms, Duty Cycle \leq 50 %
- ** When mounted on ceramic substrate of 7.5 cm² x 0.7 mm



查询"2SD1583"供应商 ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

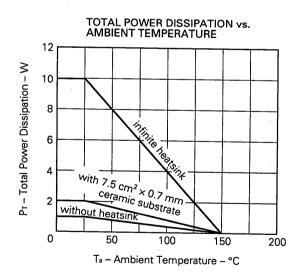
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	Ісво			10	μΑ	VcB = 20 V, IE = 0
Emitter Cutoff Current	IEBO.			10	μΑ	VEB = 5.0 V, IC = 0
DC Current Gain	hFE1*	600	2 000			VcE = 5.0 V, Ic = 50 mA
DC Current Gain	hFE2*	800	2 000	3 200		VCE = 5.0 V, IC = 0.5 A
DC Current Gain	hFE3*	500	1 400			VcE = 5.0 V, Ic = 2.0 A
Collector Saturation Voltage	VCE(sat)*		0.18	0.5	V	lc = 1.0 A, ls = 10 mA
Base Saturation Voltage	VBE(sat)*		0.85	1.2	V	Ic = 1.0 A, IB = 10 mA
Gain Bandwidth Product	fr		270		MHz	Vce = 5.0 V, le = 100 mA
Output Capacitance	Соь		20		pF	VcB = 10 V, IE = 0, f = 1.0 MH
Turn-on Time	ton		0.6		μs	
Storage Time	tstg		1.5		μs	Ic = 1A,Vcc = 10 V
Fall Time	tf		0.3		 μs	l _{B1} = -l _{B2} = 10 mA

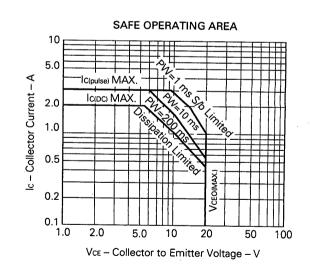
^{*} Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2 %

hre Classification

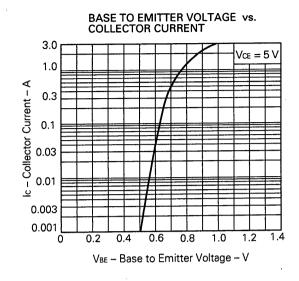
MARKING	М	L	К
hFE2	800 to 1 600	1 000 to 2 000	1 600 to 3 200

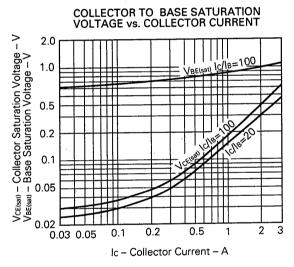
TYPICAL CHARACTERISTICS (Ta = 25 °C)

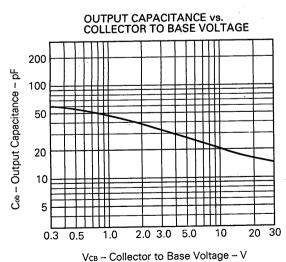


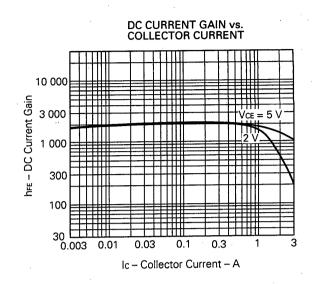


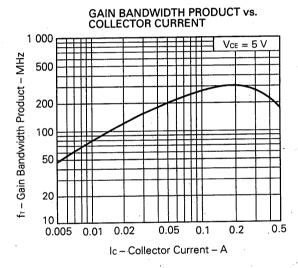
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Application note name	No.
Quality control of NEC semiconductors devices.	TEI-1202
Quality control guide of semiconductors devices.	MEI-1202
Assembly manual of semiconductors devices.	IEI-1207
Design of Push-Pull Type Switching Regulators (Basic)	TEB-1002
Design of Push-Pull Type Switching Regulators (Applications)	TEB-1003
Optimum Base Drive Conditions of Switching Power Transistors	TEB-1014

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The devices listed in this document are not suitable for use in aerospace equipment, submarine cables, nuclear reactor control systems and life support systems. If customers intend to use NEC devices for above applications or they intend to use "Standard" quality grade NEC devices for applications not intended by NEC, please contact our sales people in advance.

Application examples recommended by NEC Corporation.

Standard: Computer, Office equipment, Communication equipment, Test and Measurement equipment, Machine tools, Industrial robots, Audio and Visual equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime systems, etc.

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